#### 捷多邦,专业PCB打样工厂,24小时加急出货

# SKNH 56



询SKNH56供应

## Modules with Thyristor and Free-Wheeling Diode

#### **SKNH 56**

### **Features**

- Heat transfer through ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532
- Electrical data see also data sheet SKKH 57

### **Typical Applications**

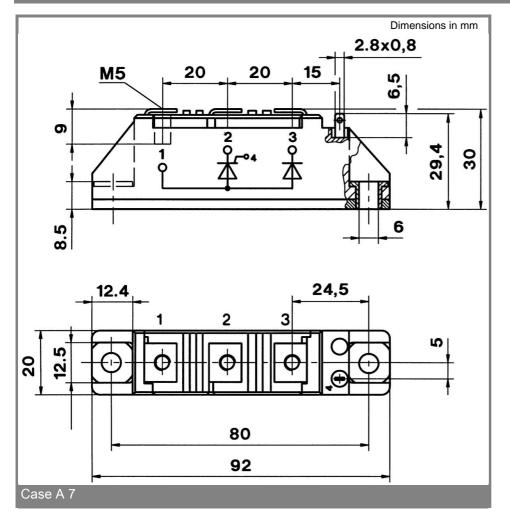
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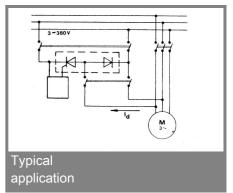
 Special modules for DC braking of AC induction motors

V <sub>RSM</sub> V	V <sub>RRM</sub> , V <sub>DRM</sub> V	$I_{TRMS} = 95 \text{ A}$ (maximum value for continuous operation) $I_{TAV} = 50 \text{ A}$ (sin. 180; $T_c = 85 \text{ °C}$ )		
1300	1200	SKNH 56/12E		, ,
1500 1700	1400 1600	SKNH 56/14E SKNH 56/16E		
1900	1800	SKNH 56/18E		

Symbol	Conditions	Values	Unit
I <sub>TAV</sub>	sin. 180; T <sub>c</sub> = 85 (100) °C	50 (35 )	Α
I <sub>D</sub>	P3/120; T <sub>a</sub> = 45 °C;	70	Α
тѕм	T <sub>vi</sub> = 25 °C; 10 ms	1500	Α
	T <sub>vj</sub> = 125 °C; 10 ms	1250	Α
²t	T <sub>vj</sub> = 25 °C; 8,3 10 ms	11000	A²s
	T <sub>vj</sub> = 125 °C; 8,3 10 ms	8000	A²s
V <sub>T</sub>	T <sub>vi</sub> = 25 °C; I <sub>T</sub> = 200 A	max. 1,65	V
/ <sub>T(TO)</sub>	T <sub>vj</sub> = 125 °C	max. 0,9	V
14.023	T <sub>vj</sub> = 125 °C	max. 3,5	mΩ
<sub>DD</sub> ; I <sub>RD</sub>	$T_{vj} = 25 \text{ °C}; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 15	mA
gd	T <sub>vj</sub> = 25 °C; I <sub>G</sub> = 1 A; di <sub>G</sub> /dt = 1 A/μs	1	μs
gr	V <sub>D</sub> = 0,67 * V <sub>DRM</sub>	2	μs
di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 100	A/µs
dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 1000	V/µs
q	T <sub>vi</sub> = 125 °C	50 150	μs
H	T <sub>vi</sub> = 25 °C; typ. / max.	/ 250	mA
L	T <sub>vi</sub> = 25 °C; R <sub>G</sub> = 33 Ω; typ. / max.	/ 600	mA
/ <sub>GT</sub>	T <sub>vi</sub> = 25 °C; d.c.	min. 3	V
GT	T <sub>vi</sub> = 25 °C; d.c.	min. 150	mA
√ <sub>GD</sub>	T <sub>vj</sub> = 125 °C; d.c.	max. 0,25	V
GD	T <sub>vj</sub> = 125 °C; d.c.	max. 6	mA
R <sub>th(j-c)</sub>	cont.; per thyristor / per diode	0,57	K/W
R <sub>th(j-c)</sub>	sin. 180; per thyristor / per diode	0,6	K/W
R <sub>th(j-c)</sub>	sin. 180; per module	0,3	K/W
R <sub>th(c-s)</sub>	per thyristor / per module	0,2 / 0,1	K/W
Γ <sub>vj</sub>	12	- 40 + 125	°C
Г <sub>stg</sub>		- 40 + 125	°C
/ <sub>isol</sub>	a. c. 50 Hz; r.m. <mark>s.; 1 s / 1 m</mark> in.	3600 / 3000	V~
М <sub>s</sub>	to heatsink	5 ± 15 %	Nm
М <sub>t</sub>	to terminals	5 ± 15 %	Nm
a 👘 👘	C.COm.	5 * 9,81	m/s²
n	approx.	120	g
Case		A 7	
		- 53	
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